

2SC 3198
2SC 3198 Ⓛ

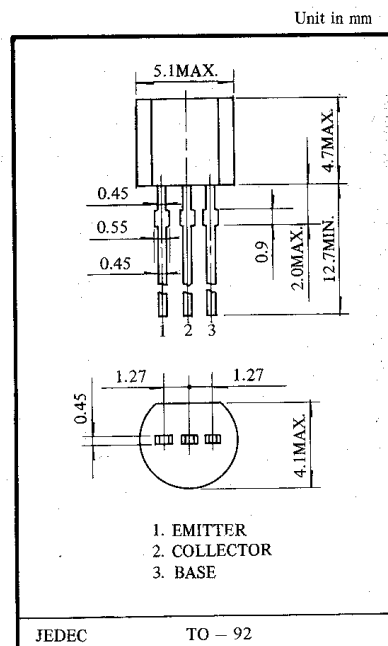
SILICON NPN TRANSISTOR EPITAXIAL PLANAR TYPE (PCT PROCESS)

APPLICATIONS

- Low Frequency Amplifiers
- Low Noise Amplifiers

FEATURES

- Excellent h_{FE} Linearity, $h_{FE}(0.1mA)/h_{FE}(2mA) = 0.95$ (Typ.)
- High h_{FE} (70~700).
- Excellent Safe Operation Area.
- Low Noise 2SC3198 NF=1dB (TYP), 10dB (Max).
2SC3198Ⓛ NF=0.2dB (TYP), 3dB (Max).
- Complementary to the 2SA1266/2SA1266Ⓛ.



MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	150	mA

CHARACTERISTIC	SYMBOL	RATING	UNIT
Emitter Current	I_E	—150	mA
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	—55~125	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut off Current	I_{CBO}	$V_{CB}=60V, I_E=0$	—	—	0.1	μA
Emitter Cut off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	—	—	0.1	μA
DC Current Gain(1)	$h_{FE(1)}$	$V_{CE}=6V, I_C=2mA$	70	—	700	—
DC Current Gain(2)	$h_{FE(2)}$	$V_{CE}=6V, I_C=150mA$	25	—	—	—
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$	—	0.1	0.25	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=100mA$	—	—	0.1	V
Transition Frequency	f_T	$V_{CE}=10V, I_E=-1mA$	80	—	—	MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	—	2.0	3.0	pF
Base Spreading Resistance	$r_{bb'}$	$V_{CB}=10V, I_E=-1mA, f=30MHz$	—	50	—	Ω
Noise Figure	2SC3198	$V_{CE}=-6V, I_C=0.1mA$ $R_g=10k\Omega, f=1KHz$	—	1	10	dB
	2SC3198Ⓛ		—	0.2	3	

■ NOTE: According to h_{FE} (1), Classified as follows

O	70-140	Y	120~240	GR	200~400	BL	350~700
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